

BC859

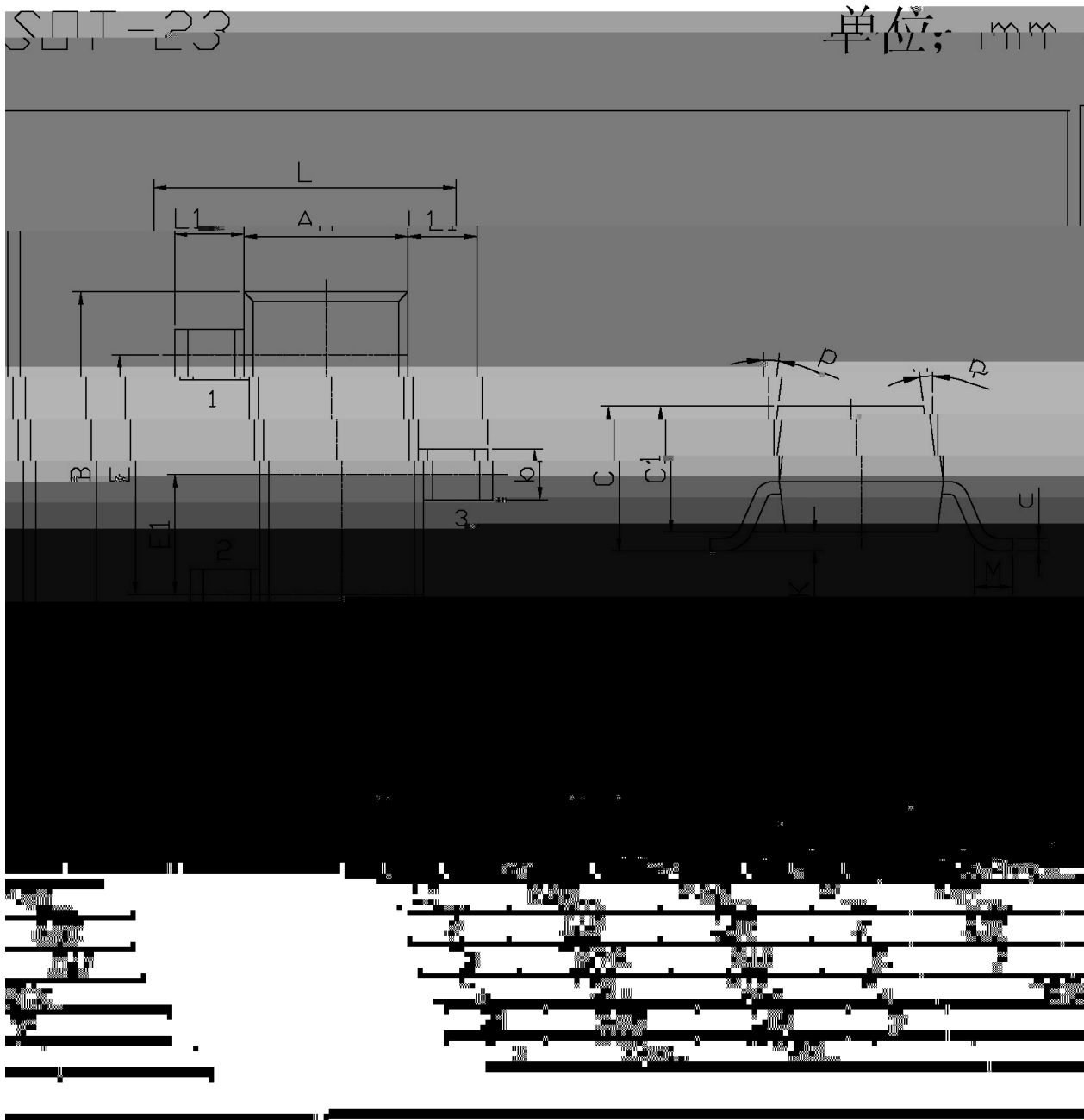
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	55 ~ 150	

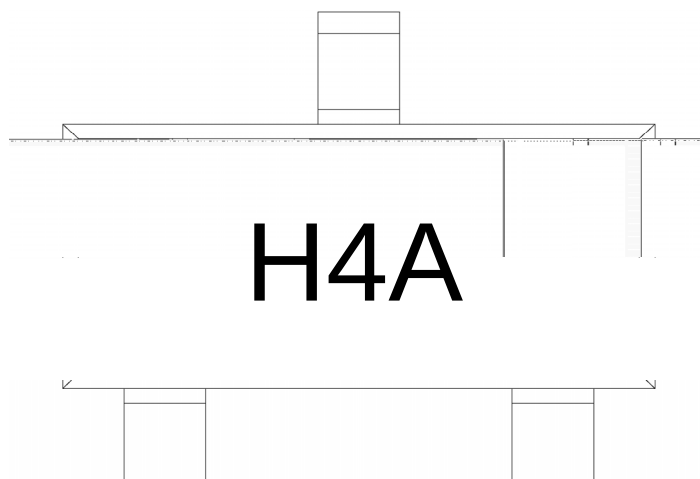
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10mA$ $I_B = 0$	-30			V
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\mu A$ $I_E = 0$	-30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -30V$ $I_E = 0$			-0.015	μA
DC Current Gain	h_{FE}	$V_{CE} = -5.0V$ $I_C = -2.0mA$	125		475	
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C = -10mA$ $I_B = -0.5mA$		-0.075	-0.3	V
	$V_{CE(sat)(2)}$	$I_C = -100mA$ $I_B = -5.0mA$		-0.25	-0.65	V
Base to Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C = -10mA$ $I_B = -0.5mA$		-0.7		V
	$V_{BE(sat)(2)}$	$I_C = -100mA$ $I_B = -5.0mA$		-0.85		V
Base to Emitter Voltage	$V_{BE(ON)(1)}$	$V_{CE} = -5.0V$ $I_C = -2.0mA$	-0.6	-0.65	-0.75	V
	$V_{BE(ON)(2)}$	$V_{CE} = -5.0V$ $I_C = -10mA$			-0.82	V
Transition Frequency	f_T	$V_{CE} = -5.0V$ $f = 100MHz$ $I_C = -10mA$		150		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V$ $f = 1.0MHz$ $I_E = 0$		4.5		pF
Noise Figure	NF	$V_{CE} = -5.0V$ $R_g = 10K\Omega$ $I_C = -200\mu A$ $f = 1.0KHz$			4.0	dB

/ Package Dimensions



/ Marking Instructions



б " X

K X № 3 " Гб

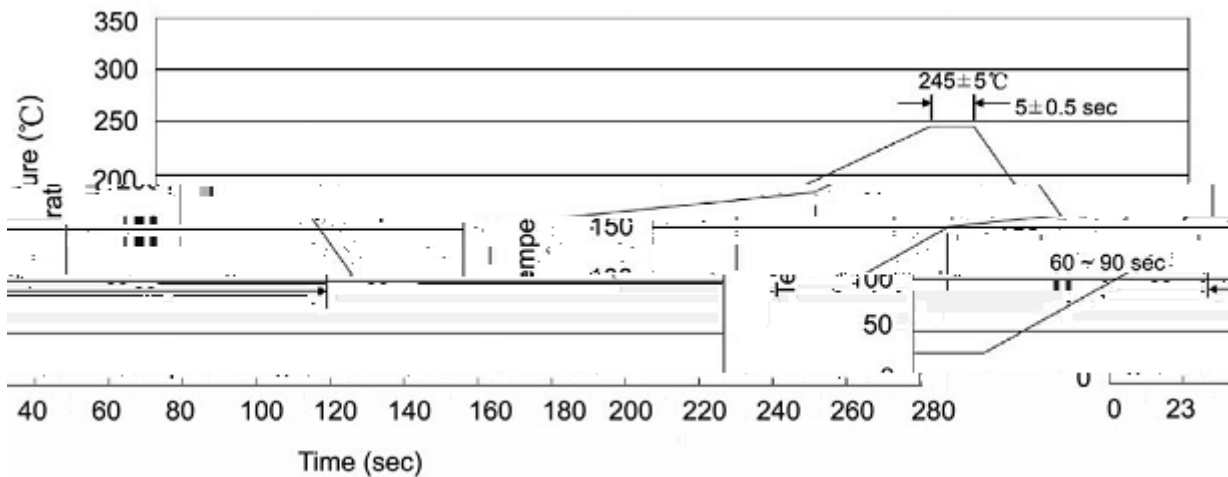
7D X № 3 " Гб

Note:

H: Company Code.

4A: Product Type Code

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



℃ /min

1. 预加热: 25~150℃, Time: 60~90sec;
2. 峰值温度: 245±5℃, Time: 5±0.5sec;
3. 冷却速度: 2~10℃/sec.

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 245±5℃, Duration: 5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

℃ /min • t s Q